优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	Package	I_D Max T_A = +25°C
-20V	52mΩ @V_{GS} = -4.5V	SOT23	-5.0A
	100mΩ @V_{GS} = -2.5V		-3.6A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

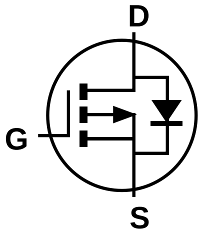
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed

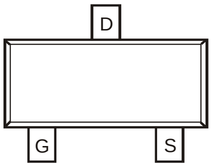
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

Top View



Internal Schematic



Top View

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-4.2 -3.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-5.0 -4.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			I_{DM}	-15	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		P_D	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	90	°C/W
	t<10s		64	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	33	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1.0	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-0.9	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	40	52	mΩ	V_{GS} = -4.5V, I_D = -4.2A
			52	100		V_{GS} = -2.5V, I_D = -3.4A
			68	200		V_{GS} = -1.8V, I_D = -2A
Forward Transfer Admittance	$\|Y_{FS}\|$	—	9	—	s	V_{DS} = -5V, I_D = -4A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	808	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	85	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	77	—	pF	
Gate Resistance	R_g		15.2		Ω	V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q_g	—	10.2	—	nC	V_{GS} = -4.5V, V_{DS} = -4V, I_D = -3.5A
Gate-Source Charge	Q_{gs}	—	1.3	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.2	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	10.8	—	ns	V_{DS} = -4V, V_{GS} = -4.5V, R_g = 6Ω, I_D = -1A
Turn-On Rise Time	t_R	—	13.7	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	79.3	—	ns	
Turn-Off Fall Time	t_F	—	34.7	—	ns	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
6. Repetitive rating, pulse width limited by junction temperature.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

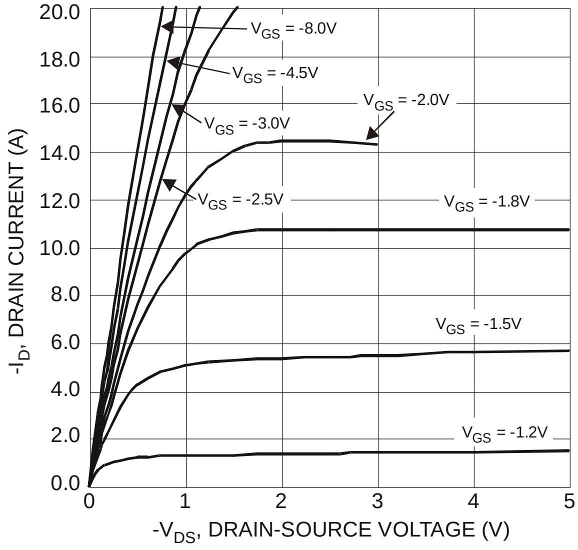


Figure 1 Typical Output Characteristics

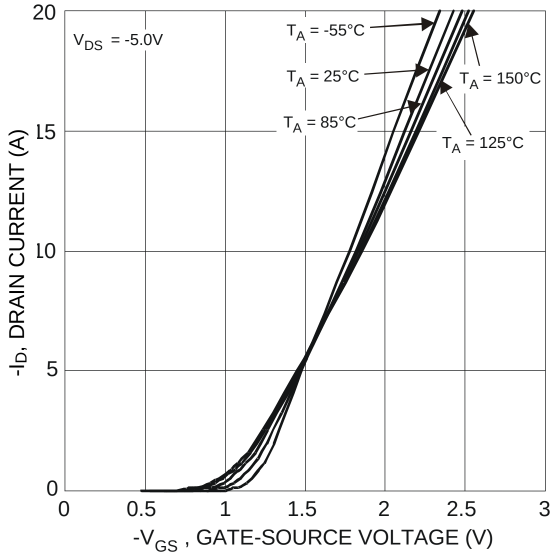


Figure 2 Typical Transfer Characteristics

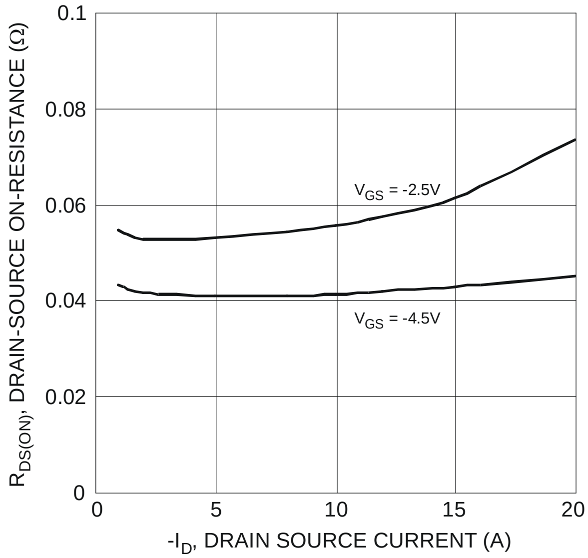


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

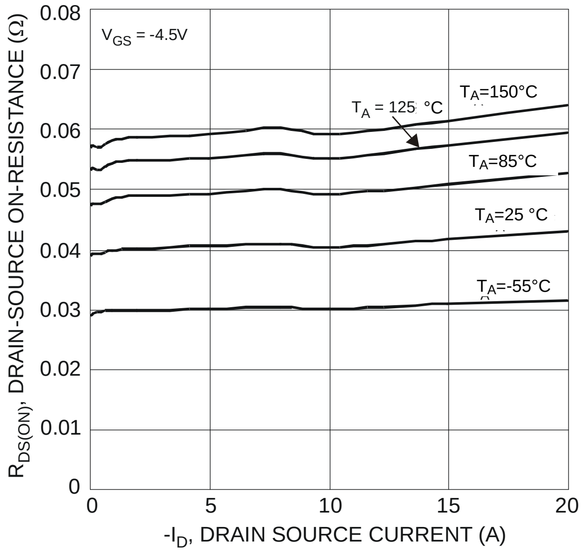


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

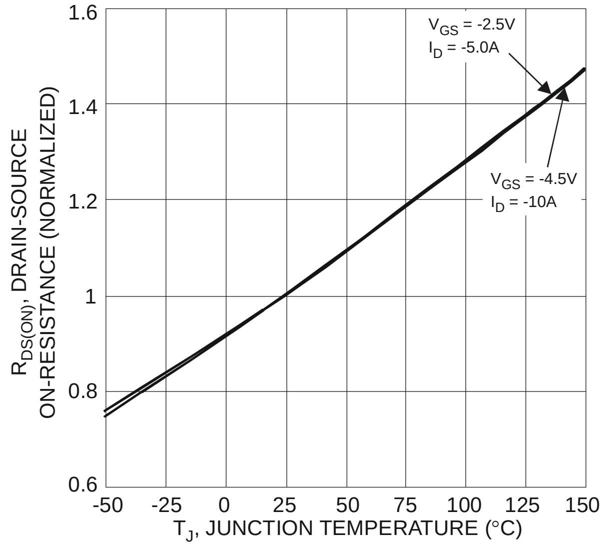


Figure 5 On-Resistance Variation with Temperature

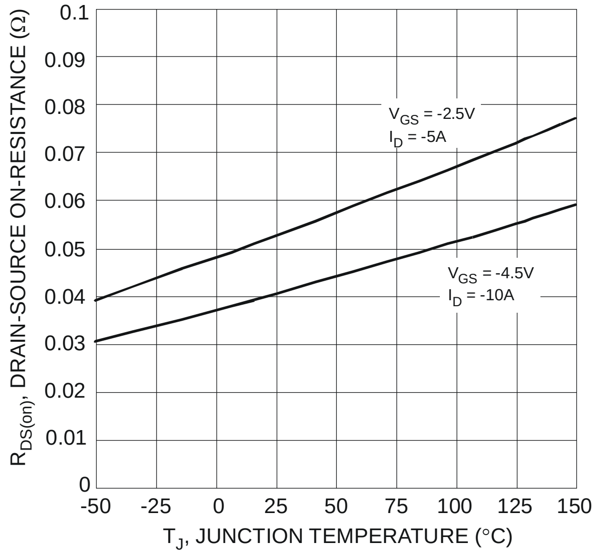


Figure 6 On-Resistance Variation with Temperature

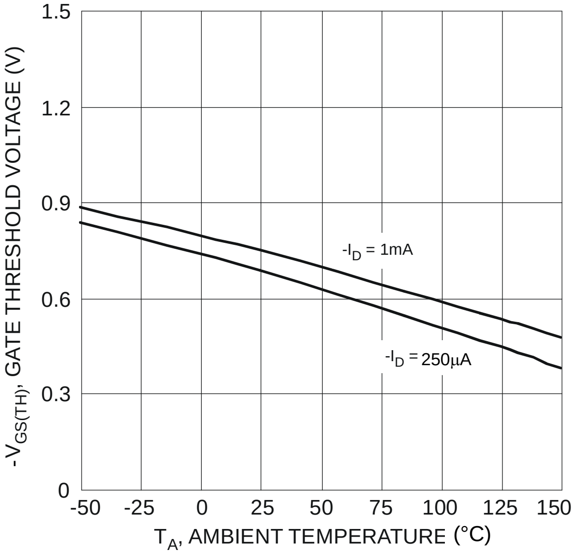


Figure 7 Gate Threshold Variation vs. Ambient Temperature

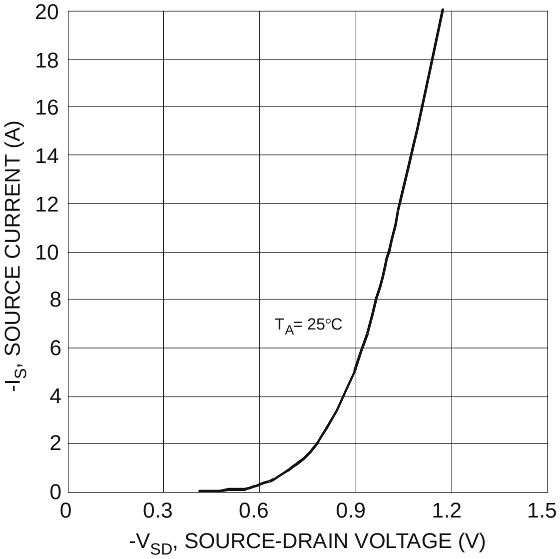


Figure 8 Diode Forward Voltage vs. Current

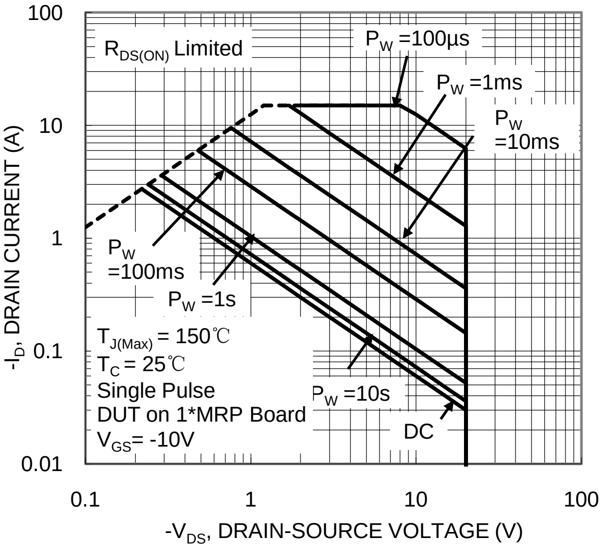
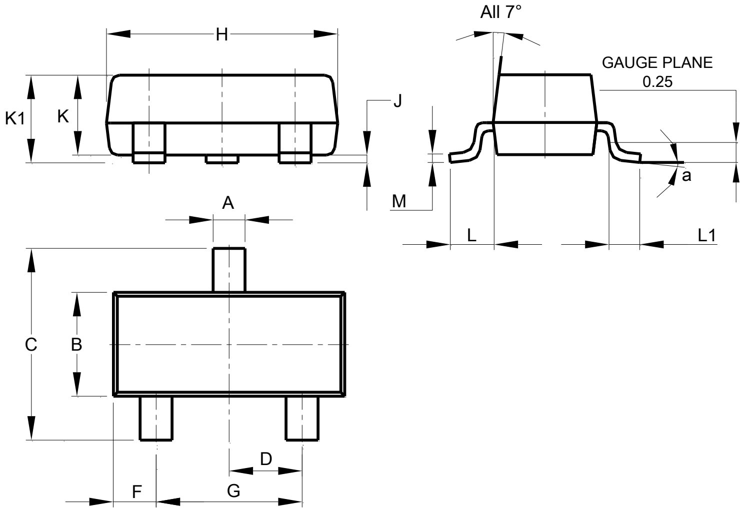


Figure 9. SOA, Safe Operation Area

Package Outline Dimensions

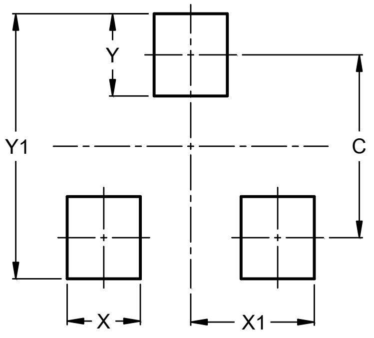
SOT23



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	–
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9